

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (previously amended): A method of fabrication of an integrated circuit, comprising the steps of:

- (a) patterning a first layer of resist on a layer of antireflective coating comprising a silicon oxynitride material and which is on a layer of gate material to define gate locations;
- (b) reducing the linewidth of said patterned layer of resist of step (a);
- (c) using said reduced linewidth patterned resist as an etch mask to form gates from said layer of gate material;
- (d) forming a layer of dielectric on said gates;
- (e) patterning a second layer of photoresist on a second layer of antireflective coating comprising a second silicon oxynitride material to define interconnects;
- (f) using said patterned photoresist without linewidth reduction to form interconnects over said gates.

Claim 2 (original): The method of claim 1, wherein:

- (a) said using of step (f) of claim 1 is using the patterned photoresist as an etch mask for an underlying layer of metal.

Claim 3 (original): The method of claim 1, wherein:

- (a) said using of step (f) of claim 1 is using the patterned photoresist as an etch mask to etch grooves in underlying dielectric to be filled with metal.

Claim 4 (previously amend d): A method of fabrication of an integrated circuit gate, comprising the steps of:

- (a) patterning a first layer of resist on an antireflective layer of a first silicon oxynitride material on a layer of dummy gate material to define gate locations;
- (b) reducing the linewidth of said patterned layer of resist of step (a);
- (c) using said reduced linewidth patterned resist as an etch mask to form dummy gates from said layer of dummy gate material;
- (d) forming a layer of dielectric adjacent said dummy gates;
- (e) removing said dummy gates;
- (f) depositing gate material on said dielectric and
- (g) patterning a second layer of photoresist on a second antireflective layer of a second silicon oxynitride material on said gate material to define gates;
- (h) using said patterned photoresist without linewidth reduction to form gates.

Claim 5 (previously added): A method of fabrication of an integrated circuit, comprising the steps of:

- (a) patterning a first layer of resist on a first layer of antireflective coating comprising a first silicon oxynitride material and which is on a layer of gate material to define gate locations;
- (b) using said patterned resist of step (a) as an etch mask to form gates from said layer of gate material;
- (c) forming a layer of dielectric on said gates;
- (d) patterning a second layer of resist on a second layer of antireflective coating comprising a second silicon oxynitride material to define interconnects;
- (e) using said patterned resist of step (d) to form interconnects over said gates.

Appl.No.: 09/092,115
Amendment dated April 10, 2004
Response to Office Action mailed January 21, 2004

Claim 6 (previously added): The method of claim 5, wherein:

(a) said using of step (e) of claim 5 is using the patterned resist as an etch mask for an underlying layer of metal.

Claim 7 (previously added): The method of claim 5, wherein:

(a) said using of step (e) of claim 5 is using the patterned resist as an etch mask to etch grooves in underlying dielectric to be filled with metal.